

Gabriel Vanko

List of Publications by Year in descending order

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25
papers

179
citations

1163117

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1125743

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25
all docs

25
docs citations

25
times ranked

227
citing authors

#	ARTICLE	IF	CITATIONS
1	Bulk micromachining of SiC substrate for MEMS sensor applications. <i>Microelectronic Engineering</i> , 2013, 110, 260-264.	2.4	31
2	AlGaIn/GaN C-HEMT structures for dynamic stress detection. <i>Sensors and Actuators A: Physical</i> , 2011, 172, 98-102.	4.1	20
3	Carbide-free one-zone sulfurization method grows thin MoS ₂ layers on polycrystalline CVD diamond. <i>Scientific Reports</i> , 2019, 9, 2001.	3.3	19
4	Selective area deposition of diamond films on AlGaIn/GaN heterostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2014, 251, 2574-2580.	1.5	15
5	GaN/SiC based surface acoustic wave structures for hydrogen sensors with enhanced sensitivity. <i>Sensors and Actuators A: Physical</i> , 2015, 227, 55-62.	4.1	15
6	Pt/NiO ring gate based Schottky diode hydrogen sensors with enhanced sensitivity and thermal stability. <i>Sensors and Actuators B: Chemical</i> , 2014, 202, 1-8.	7.8	14
7	Study on electronic properties of diamond/SiN _x -coated AlGaIn/GaN high electron mobility transistors operating up to 500°C. <i>Diamond and Related Materials</i> , 2018, 89, 266-272.	3.9	9
8	Temperature-dependent stress in diamond-coated AlGaIn/GaN heterostructures. <i>Materials and Design</i> , 2016, 106, 305-312.	7.0	8
9	Diamond-coated three-dimensional GaN micromembranes: Effect of nucleation and deposition techniques. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 2585-2590.	1.5	7
10	Influence of Diamond CVD Growth Conditions and Interlayer Material on Diamond/GaN Interface. <i>Materials Science Forum</i> , 2015, 821-823, 982-985.	0.3	7
11	Impact of Ir gate interfacial oxide layers on performance of AlGaIn/GaN HEMT. <i>Applied Surface Science</i> , 2013, 267, 159-163.	6.1	6
12	Uncooled Antenna-Coupled Microbolometer for Detection of Terahertz Radiation. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2021, 42, 462-478.	2.2	6
13	Additive Manufacturing in Atomic Layer Processing Mode. <i>Small Methods</i> , 2022, 6, e2101546.	8.6	6
14	Ohmic contacts to p-GaN Using Au/Ni-Mg-O Metallization. <i>Journal of Electrical Engineering</i> , 2010, 61, 378-381.	0.7	4
15	AlGaIn/GaN Based SAW-HEMT Devices for Chemical Gas Sensors Operating in GHz Range. <i>Procedia Engineering</i> , 2011, 25, 1101-1104.	1.2	4
16	Ir/Al multilayer Gates for High Temperature Operated AlGaIn/GaN HEMTs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1700691.	1.8	3
17	Modal Analysis of Gallium Nitride Membrane for Pressure Sensing Device. <i>Key Engineering Materials</i> , 0, 605, 404-407.	0.4	2
18	AlGaIn/GaN C-HEMT structures for dynamic stress detection. <i>Procedia Engineering</i> , 2010, 5, 1405-1408.	1.2	1

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19	MEMS pressure sensor fabricated by advanced bulk micromachining techniques. Proceedings of SPIE, 2013, , .	0.8	1
20	Enhanced Sensitivity of Pt/NiO Gate Based AlGaIn/GaN C-HEMT Hydrogen Sensor. Key Engineering Materials, 2014, 605, 491-494.	0.4	1
21	Microwave Characterization and Properties of 2 ¹ / ₄ m Gate Length AlGaIn/GaN HEMT Structures. , 2008, , .		0
22	4H-SiC and novel SI GaAs-based M-S-M radiation hard photodetectors applicable in UV, EUV, and soft x-ray detection: design, technology, and performance testing. Proceedings of SPIE, 2013, , .	0.8	0
23	Fabrication of Diamond Membranes by Femtosecond Laser Ablation for MEMS Sensor Applications. Proceedings (mdpi), 2020, 56, .	0.2	0
24	Influence of SiON interlayer on the diamond/GaN heterostructures studied by Raman and SIMS measurements. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2021, 273, 115434.	3.5	0
25	Direct Deposition of CVD Diamond Layers on Top of GaN Membranes. Proceedings (mdpi), 2020, 56, .	0.2	0